

# Phase Control Thyristors (Hockey PUK Version), 560 A



**B-PUK (TO-200AC)** 

| PRIMARY CHARACTERISTICS            |   |  |  |  |
|------------------------------------|---|--|--|--|
| I <sub>T(AV)</sub>                 | 560 A   |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> | 400 V, 800 V, 1200 V, 1600 V,<br>1800 V, 2000 V |  |  |  |
| $V_{TM}$                           | 2.18 V  |  |  |  |
| I <sub>GT</sub>                    | 100 mA  |  |  |  |
| $T_J$                              | -40 °C to +125 °C                               |  |  |  |
| Package                            | B-PUK (TO-200AC)                                |  |  |  |
| Circuit configuration              | Single SCR                                      |  |  |  |

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

| MAJOR RATINGS AND CHARACTERISTICS  |                 |             |                   |  |  |  |
|------------------------------------|-----------------|-------------|-------------------|--|--|--|
| PARAMETER                          | TEST CONDITIONS | VALUES      | UNITS             |  |  |  |
| <b>L</b>                           |                 | 560         | A                 |  |  |  |
| I <sub>T(AV)</sub>                 | T <sub>hs</sub> | 55          | °C                |  |  |  |
| L                                  |                 | 1115        | A                 |  |  |  |
| I <sub>T(RMS)</sub>                | T <sub>hs</sub> | 25          | °C                |  |  |  |
|                                    | 50 Hz           | 8000        | ^                 |  |  |  |
| I <sub>TSM</sub>                   | 60 Hz           | 8380        | A A               |  |  |  |
| l <sup>2</sup> t                   | 50 Hz           | 320         | kA <sup>2</sup> s |  |  |  |
| I=1                                | 60 Hz           | 292         | KA-S              |  |  |  |
| V <sub>DRM</sub> /V <sub>RRM</sub> |                 | 400 to 2000 | V                 |  |  |  |
| tq                                 | Typical         | 100         | μs                |  |  |  |
| TJ                                 |                 | -40 to 125  | °C                |  |  |  |

#### **ELECTRICAL SPECIFICATIONS**

| VOLTAGE RATINGS  |                 |  |  |   |  |  |  |  |
|------------------|-----------------|--|--|---|--|--|--|--|
| TYPE NUMBER      | VOLTAGE<br>CODE | V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE<br>PEAK AND OFF-STATE VOLTAGE<br>V | V <sub>RSM</sub> , MAXIMUM<br>NON-REPETITIVE PEAK VOLTAGE<br>V | $I_{DRM}/I_{RRM}$ MAXIMUM<br>AT $T_J = T_J$<br>MAXIMUM mA |  |  |  |  |
|                  | 04              | 400  | 500  |   |  |  |  |  |
| 08<br>VS-ST300CL |                 | 800  | 900  |   |  |  |  |  |
|                  |                 | 1200   | 1300   | 50  |  |  |  |  |
| VO 010000L       | 16              | 1600   | 1700   | 30  |  |  |  |  |
| 18               |                 | 1800   | 1900   |   |  |  |  |  |
|                  | 20              | 2000   | 2100   |   |  |  |  |  |



| ABSOLUTE MAXIMUM RATINGS                      |                     |  |  |   | VALUES    | _                   |
|---|---------------------|--|--|---|-----------|---------------------|
| PARAMETER                                     | SYMBOL              |  | TEST CONDITIONS  |   |           | UNITS               |
| Maximum average on-state current              | 1                   | 180° condu   | ction, half sine v   | vave  | 560 (275) | Α                   |
| at heatsink temperature                       | I <sub>T(AV)</sub>  | double side  | (single side) co   | oled  | 55 (75)   | °C                  |
| Maximum RMS on-state current                  | I <sub>T(RMS)</sub> | DC at 25 °C  | heatsink tempe   | erature double side cooled                        | 1115      |                     |
|   |                     | t = 10 ms  | No voltage   |   | 8000      |                     |
| Maximum peak, one-cycle                       |                     | t = 8.3 ms   | reapplied  |   | 8380      | A kA <sup>2</sup> s |
| non-repetitive surge current                  | I <sub>TSM</sub>    | t = 10 ms  | 100 % V <sub>RRM</sub>   | Sinusoidal half wave, initial $T_J = T_J$ maximum | 6730      |                     |
|   |                     | t = 8.3 ms   | reapplied  |   | 7040      |                     |
| Maximum I <sup>2</sup> t for fusing           |                     | t = 10 ms  | No voltage reapplied   |   | 320       |                     |
|   | l <sup>2</sup> t    | t = 8.3 ms   |  |   | 292       |                     |
|   |                     | t = 10 ms  |  |   | 226       |                     |
|   |                     | t = 8.3 ms   | reapplied  |   | 207       |                     |
| Maximum I <sup>2</sup> √t for fusing          | I <sup>2</sup> √t   | t = 0.1 to 10 ms, no voltage reapplied   |  |   | 3200      | kA²√s               |
| Low level value of threshold voltage          | V <sub>T(TO)1</sub> | (16.7 % x π  | (16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum |   |           | V                   |
| High level value of threshold voltage         | V <sub>T(TO)2</sub> | $(I > \pi \times I_{T(AV)})$   | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$                        |   |           | V                   |
| Low level value of on-state slope resistance  | r <sub>t1</sub>     | (16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum         |  |   | 0.74      | mΩ                  |
| High level value of on-state slope resistance | r <sub>t2</sub>     | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$                              |  |   | 0.73      | 11122               |
| Maximum on-state voltage                      | $V_{TM}$            | $I_{pk} = 1635 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$ |  |   | 2.18      | ٧                   |
| Maximum holding current                       | I <sub>H</sub>      | T 05 °C  | T 05 00 and a col 40 V acidi a l   |   |           | mA                  |
| Typical latching current                      | ΙL                  | T <sub>J</sub> = 25 °C, anode supply 12 V resistive load                             |  |   | 1000      | 11174               |

| SWITCHING  |                |   |        |       |  |  |
|--|----------------|---|--------|-------|--|--|
| PARAMETER  | SYMBOL         | TEST CONDITIONS   | VALUES | UNITS |  |  |
| Maximum non-repetitive rate of rise of turned-on current | dI/dt          | Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$                         | 1000   | A/μs  |  |  |
| Typical delay time                                       | t <sub>d</sub> | Gate current 1 A, $dl_g/dt = 1 A/\mu s$<br>$V_d = 0.67 \% V_{DRM}, T_J = 25 °C$   | 1.0    |       |  |  |
| Typical turn-off time                                    | t <sub>q</sub> | $I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/μs, $V_R$ = 50 V, dV/dt = 20 V/μs, gate 0 V 100 $\Omega$ , $t_p$ = 500 μs | 100    | μs    |  |  |

| BLOCKING   |                                       |   |        |       |  |
|--|---------------------------------------|---|--------|-------|--|
| PARAMETER  | SYMBOL                                | TEST CONDITIONS   | VALUES | UNITS |  |
| Maximum critical rate of rise of off-state voltage | dV/dt                                 | T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub> | 500    | V/µs  |  |
| Maximum peak reverse and off-state leakage current | I <sub>RRM,</sub><br>I <sub>DRM</sub> | $T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied                          | 50     | mA    |  |



| TRIGGERING                          |                    |   |  |        |      |       |
|-------------------------------------|--------------------|---|--|--------|------|-------|
| DADAMETED                           | CVMDOL             | TEST CONDITIONS   |  | VALUES |      | шито  |
| PARAMETER                           | SYMBOL             |   |  | TYP.   | MAX. | UNITS |
| Maximum peak gate power             | P <sub>GM</sub>    | $T_J = T_J$ maximum,  | $t_p \le 5 \text{ ms}$   | 10     | 0.0  | w     |
| Maximum average gate power          | P <sub>G(AV)</sub> | $T_J = T_J$ maximum,  | f = 50 Hz, d% = 50   | 2      | .0   | VV    |
| Maximum peak positive gate current  | I <sub>GM</sub>    | $T_J = T_J$ maximum,  | $t_p \le 5 \text{ ms}$   | 3      | .0   | Α     |
| Maximum peak positive gate voltage  | + V <sub>GM</sub>  | T. T in i   |  | 20     |      | V     |
| Maximum peak negative gate voltage  | - V <sub>GM</sub>  | $T_J = T_J$ maximum, $t_p \le 5$ ms                         |  |        | .0   | V     |
|                                     |                    | T <sub>J</sub> = - 40 °C                                    | Maximum required gate trigger/<br>current/voltage are the lowest   | 200    | -    |       |
| DC gate current required to trigger | I <sub>GT</sub>    | T <sub>J</sub> = 25 °C                                      |  | 100    | 200  | mA    |
|                                     |                    | T <sub>J</sub> = 125 °C                                     |  | 50     | -    |       |
|                                     |                    | T <sub>J</sub> = - 40 °C value which will trigger all units | 2.5  | -      |      |       |
| DC gate voltage required to trigger | $V_{GT}$           | T <sub>J</sub> = 25 °C                                      | 12 V anode to cathode applied  | 1.8    | 3.0  | V     |
|                                     |                    | T <sub>J</sub> = 125 °C                                     |  | 1.1    | -    |       |
| DC gate current not to trigger      | $I_{GD}$           |   | Maximum gate current/  | 10     | 0.0  | mA    |
| DC gate voltage not to trigger      | $V_{\mathrm{GD}}$  | $T_J = T_J$ maximum   | voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied | 0.25   |      | V     |

| THERMAL AND MECHANICAL SPECIFICATIONS             |                     |   |             |        |  |
|---|---------------------|---|-------------|--------|--|
| PARAMETER   | SYMBOL              | TEST CONDITIONS                               | VALUES      | UNITS  |  |
| Maximum operating junction temperature range      | $T_J$               |   | -40 to 125  | - °C   |  |
| Maximum storage temperature range                 | T <sub>Stg</sub>    |   | -40 to 150  | , C    |  |
| Maximum thermal resistance, junction to heatsink  | D                   | DC operation single side cooled               | 0.11        |        |  |
| maximum thermal resistance, junction to heatslink | R <sub>thJ-hs</sub> | DC operation double side cooled               | 0.05        | K/W    |  |
|   | R <sub>thC-hs</sub> | DC operation single side cooled               | 0.011       |        |  |
| Maximum thermal resistance, case to heatsink      |                     | DC operation double side cooled               | 0.006       |        |  |
| Mounting force, ± 10 %                            |                     |   | 9800        | N      |  |
| Woulding force, ± 10 %                            |                     |   | (1000)      | (kg)   |  |
| Approximate weight                                |                     |   | 250         | g      |  |
| Case style  |                     | See dimensions - link at the end of datasheet | B-PUK (TO-2 | 200AC) |  |

| △R <sub>thJ-hs</sub> CONDUCTION |                       |             |                        |             |                     |       |
|---------------------------------|-----------------------|-------------|------------------------|-------------|---------------------|-------|
| CONDUCTION ANGLE                | SINUSOIDAL CONDUCTION |             | RECTANGULAR CONDUCTION |             | TEST CONDITIONS     | UNITS |
| CONDUCTION ANGLE                | SINGLE SIDE           | DOUBLE SIDE | SINGLE SIDE            | DOUBLE SIDE | TEST CONDITIONS     | UNITS |
| 180°                            | 0.012                 | 0.010       | 0.008                  | 0.008       |                     |       |
| 120°                            | 0.014                 | 0.015       | 0.014                  | 0.014       | $T_J = T_J$ maximum | K/W   |
| 90°                             | 0.018                 | 0.018       | 0.019                  | 0.019       |                     |       |
| 60°                             | 0.026                 | 0.027       | 0.027                  | 0.028       |                     |       |
| 30°                             | 0.045                 | 0.046       | 0.046                  | 0.046       |                     |       |

#### Note

• The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

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## Vishay Semiconductors

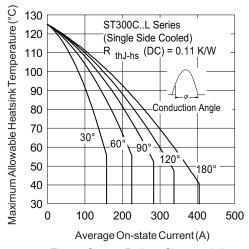


Fig. 1 - Current Ratings Characteristics

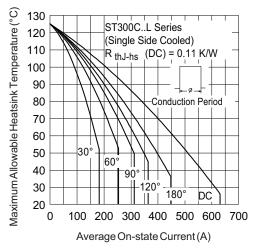


Fig. 2 - Current Ratings Characteristics

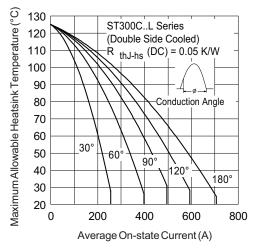


Fig. 3 - Current Ratings Characteristics

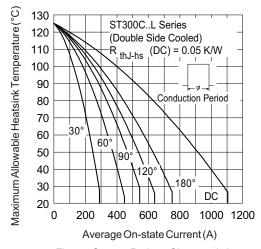


Fig. 4 - Current Ratings Characteristics

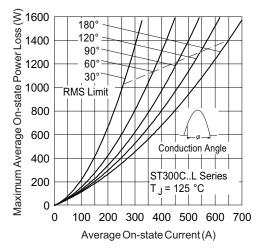


Fig. 5 - On-State Power Loss Characteristics

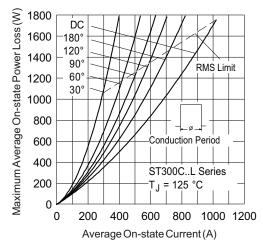
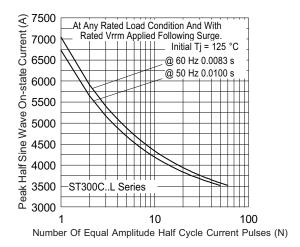


Fig. 6 - On-State Power Loss Characteristics



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Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

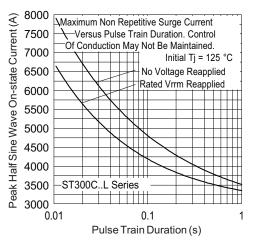


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

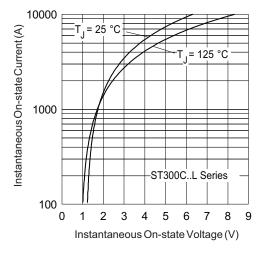


Fig. 9 - On-State Voltage Drop Characteristcs

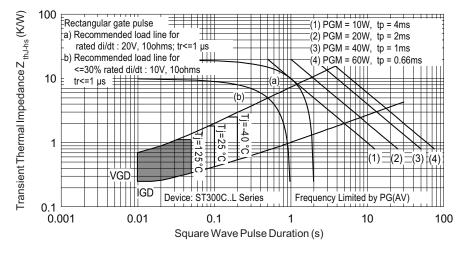


Fig. 1 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

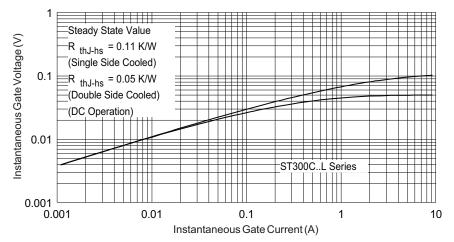
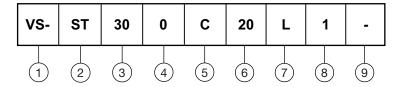


Fig. 10 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

**8** - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

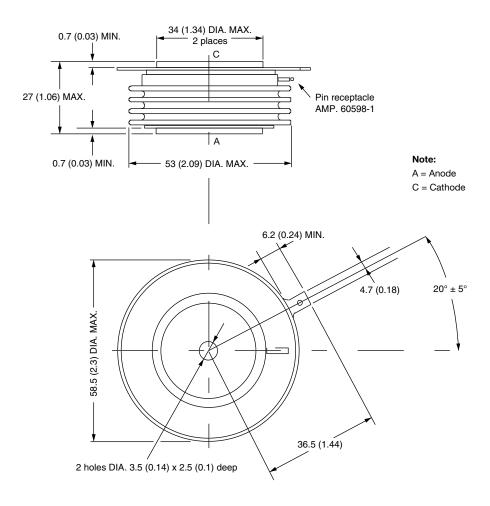
| LINKS TO RELATED DOCUMENTS |                          |  |  |
|----------------------------|--------------------------|--|--|
| Dimensions                 | www.vishay.com/doc?95076 |  |  |



# **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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